



# N-Channel Enhancement Mode Field Effect Transistor

## Product Summary

DS

30V





# YJS18N03A

## Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
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Static Parameter



Typical Performance Characteristics

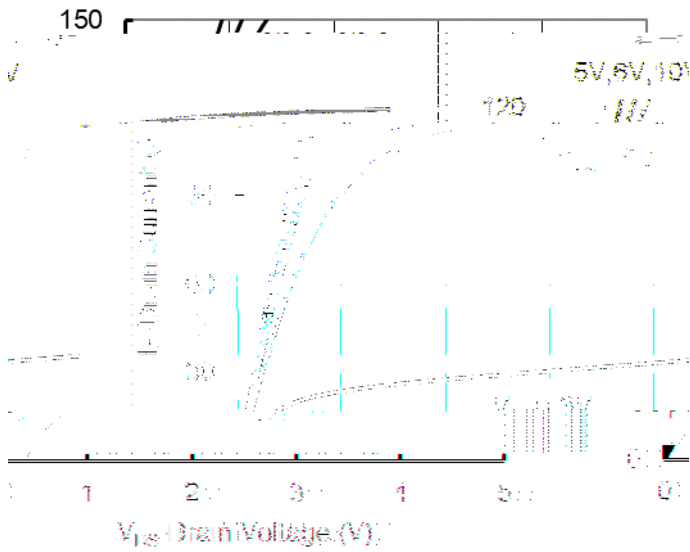


Figure 1. Output Characteristics

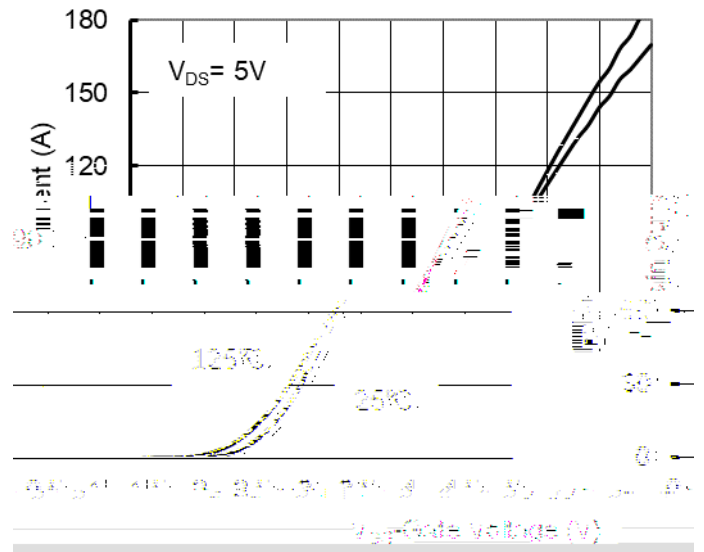


Figure 2. Transfer Characteristics

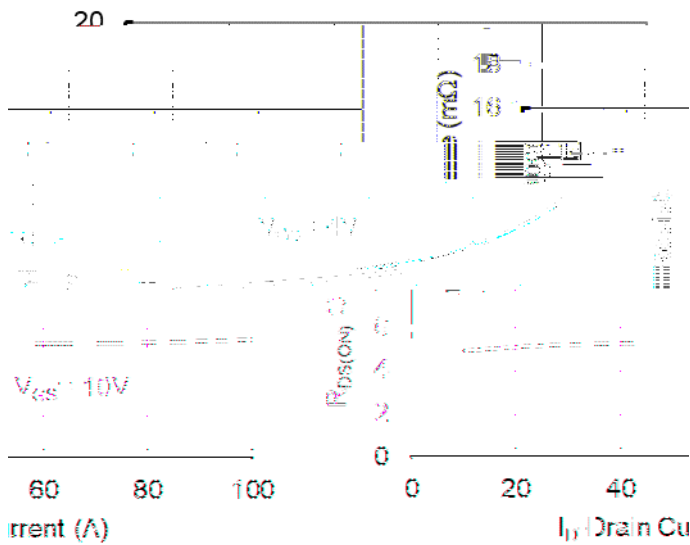


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

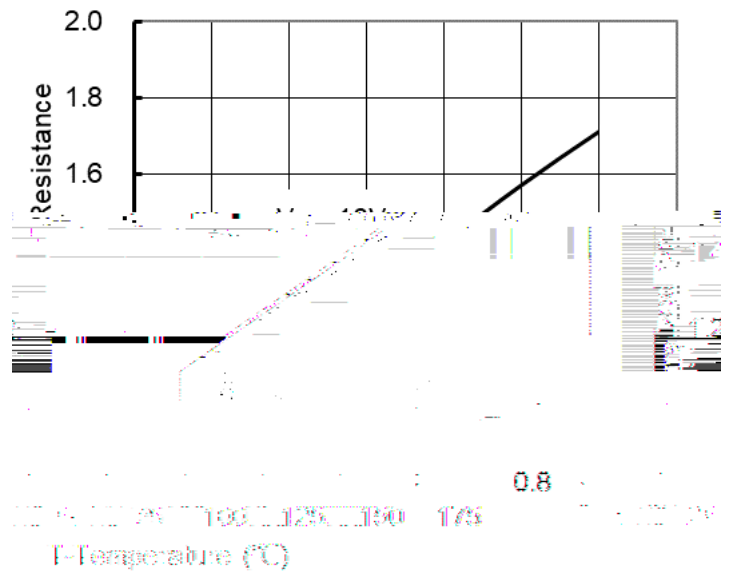


Figure 4. On-Resistance vs. Junction Temperature

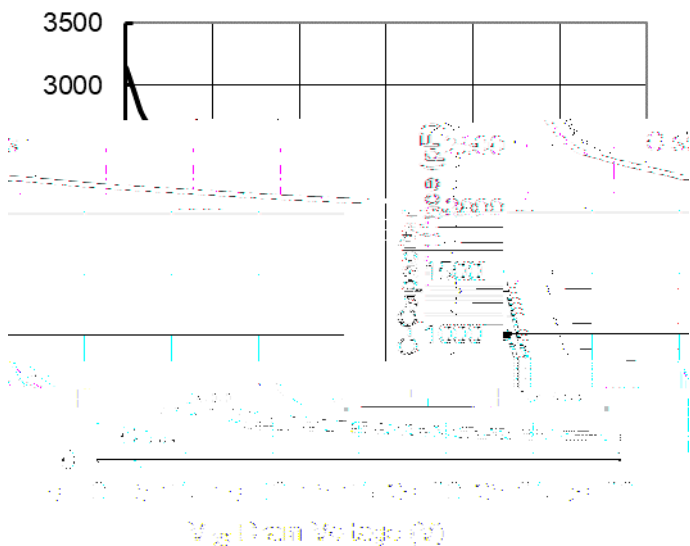


Figure 5. Capacitance Characteristics

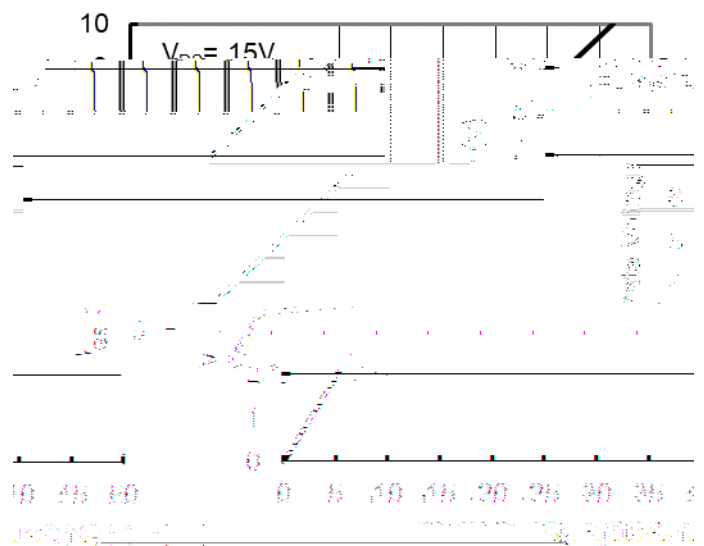
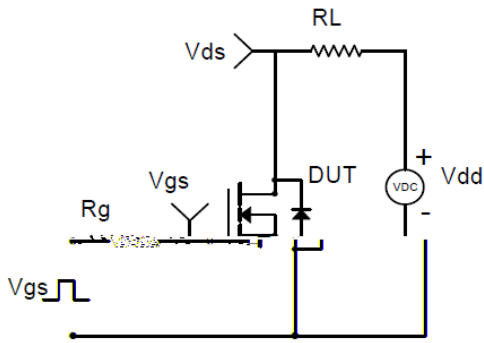
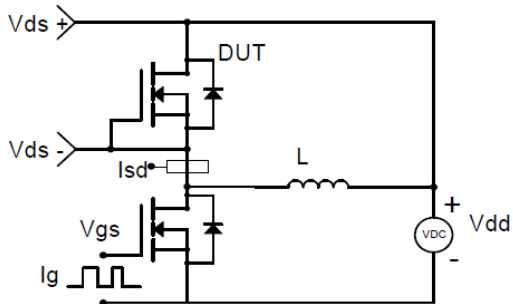


Figure 6. Gate Charge

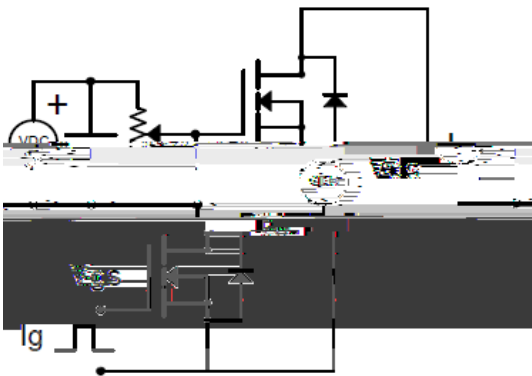




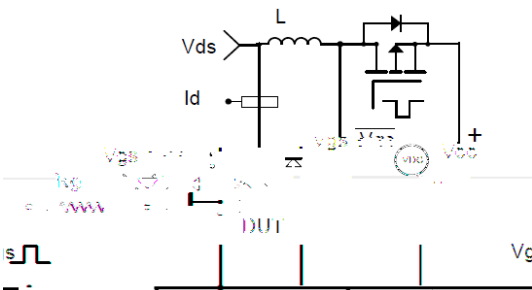
**Resistive Switching Test Circuit & Waveforms**



**Diode Recovery Test Circuit & Waveforms**



**Gate Charge Test Circuit & Waveform**



**Unclamped Inductive Switching (UIS) Test Circuit & Waveforms**





## Disclaimer

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